

# Cheng Tai Kuo

## List of Publications by Year in descending order

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times ranked

1547

citing authors

#	ARTICLE	IF	CITATIONS
1	Exfoliation and Raman Spectroscopic Fingerprint of Few-Layer NiPS3 Van der Waals Crystals. <i>Scientific Reports</i> , 2016, 6, 20904.	3.3	222
2	Plasmonic Green Nanolaser Based on a Metalâ€“Oxideâ€“Semiconductor Structure. <i>Nano Letters</i> , 2011, 11, 4256-4260.	9.1	106
3	Absence of Fermi-Level Pinning at Cleaved Nonpolar InN Surfaces. <i>Physical Review Letters</i> , 2008, 101, 106803.	7.8	87
4	Is electron accumulation universal at InN polar surfaces?. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	46
5	Cross-sectional scanning photoelectron microscopy and spectroscopy of wurtzite InNâ€“GaN heterojunction: Measurement of â€œintrinsicâ€ band lineup. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	39
6	Polarization-induced valence-band alignments at cation- and anion-polar InNâ€“GaN heterojunctions. <i>Applied Physics Letters</i> , 2007, 91, .	3.3	35
7	Experimental Determination of Electron Affinities for InN and GaN Polar Surfaces. <i>Applied Physics Express</i> , 2012, 5, 031003.	2.4	35
8	Valence band offset and interface stoichiometry at epitaxial Si3N4/Si(111) heterojunctions formed by plasma nitridation. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	22
9	Interface properties and built-in potential profile of a $\text{LaCr}_{3-x}\text{SrTi}_{3.2}\text{O}_{9-x}$ superlattice determined by standing-wave excited photoemission spectroscopy. <i>Physical Review B</i> , 2018, 97, 224102.	3.3	22
10	Element- and momentum-resolved electronic structure of the dilute magnetic semiconductor manganese doped gallium arsenide. <i>Nature Communications</i> , 2018, 9, 3306.	12.8	22
11	Immobilization of DNA-Au nanoparticles on aminosilane-functionalized aluminum nitride epitaxial films for surface acoustic wave sensing. <i>Applied Physics Letters</i> , 2008, 93, .	3.3	19
12	Effects of (NH4)2Sx treatment on indium nitride surfaces. <i>Journal of Applied Physics</i> , 2010, 107, 043710.	2.5	18
13	X-ray Absorption Spectroscopy Study of the Effect of Rh doping in Sr2IrO4. <i>Scientific Reports</i> , 2016, 6, 23856.	3.3	15
14	Natural band alignments of InN/GaN/AlN nanorod heterojunctions. <i>Applied Physics Letters</i> , 2011, 99, 122101.	3.3	14
15	The energy band alignment at the interface between mechanically exfoliated few-layer NiPS3 nanosheets and ZnO. <i>Current Applied Physics</i> , 2016, 16, 404-408.	2.4	14
16	Characterization of free-standing InAs quantum membranes by standing wave hard x-ray photoemission spectroscopy. <i>APL Materials</i> , 2018, 6, .	5.1	11
17	Insulating-layer formation of metallic LaNiO3 on Nb-doped SrTiO3 substrate. <i>Applied Physics Letters</i> , 2015, 106, 121601.	3.3	10
18	Superconductor to Mott insulator transition in YBa2Cu3O7/LaCaMnO3 heterostructures. <i>Scientific Reports</i> , 2016, 6, 33184.	3.3	10

#	ARTICLE	IF	CITATIONS
19	Direct imaging of GaN p-n junction by cross-sectional scanning photoelectron microscopy and spectroscopy. <i>Applied Physics Letters</i> , 2009, 94, .	3.3	9
20	Hard x-ray standing-wave photoemission insights into the structure of an epitaxial Fe/MgO multilayer magnetic tunnel junction. <i>Journal of Applied Physics</i> , 2019, 126, 075305.	2.5	9
21	Two-dimensional electron systems in perovskite oxide heterostructures: Role of the polarity-induced substitutional defects. <i>Physical Review Materials</i> , 2020, 4, .	2.4	7
22	Spontaneous-polarization-induced heterojunction asymmetry in III-nitride semiconductors. <i>Applied Physics Letters</i> , 2011, 99, 022113.	3.3	6
23	Depth-resolved resonant inelastic x-ray scattering at a superconductor/half-metallic-ferromagnet interface through standing wave excitation. <i>Physical Review B</i> , 2018, 98, .	3.2	6
24	Orientation-Controlled Anisotropy in Single Crystals of Quasi-1D BaTiS <sub>3</sub> . <i>Chemistry of Materials</i> , 2022, 34, 5680-5689.	6.7	6
25	Atomic-layer-resolved composition and electronic structure of the cuprate $B_{2-x}Ca_xCuO_3$ Interface Carriers and Enhanced Electron-Phonon Coupling Effect in Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> Heterostructure Revealed by Resonant Inelastic Soft X-Ray Scattering. <i>Advanced Functional Materials</i> , 2021, 31, 2104430.	3.2	5
26	High resolution depth profiling using near-total-reflection hard x-ray photoelectron spectroscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	2.1	5
27	Nitride Semiconductor Nanorod Heterostructures for Full-Color and White-Light Applications. <i>Semiconductors and Semimetals</i> , 2017, 96, 341-384.	0.7	3
28	Orbital contributions in the element-resolved valence electronic structure of Bi <sub>2</sub> Ca <sub>2</sub> Mn <sub>3</sub> O <sub>10</sub> . <i>Physical Review B</i> , 2021, 104, .	2.1	2
29	Emergent phenomena at oxide interfaces studied with standing-wave photoelectron spectroscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022, 40, 020801.	2.1	2
30	Probing the polar-nonpolar oxide interfaces using resonant x-ray standing wave techniques. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022, 40, 010804.	2.1	1
31	Electronic Properties of III-Nitride Surfaces and Interfaces Studied by Scanning Photoelectron Microscopy and Spectroscopy. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1202, 38.	0.1	0